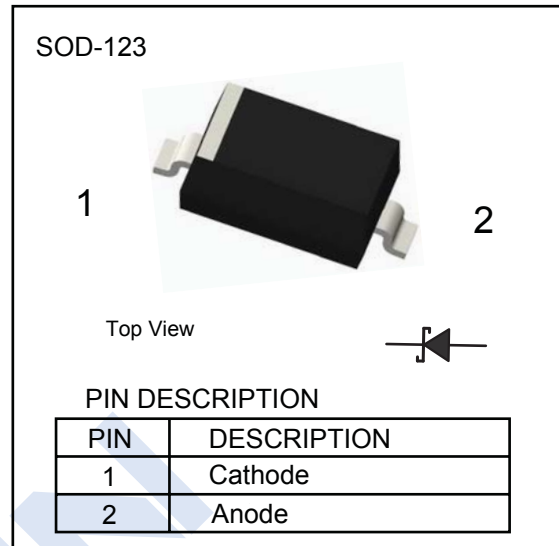


Schottky Diodes

1KK2004E

■ Features

- Low Forward Voltage Drop.
- Fast Switching Time.

■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	40	V
Working Peak Reverse Voltage	V_{RWM}		
DC Reverse Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	28	
Non-Repetitive Peak Forward Current	I_{FM}	350	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	1.5	A
Power Dissipation	P_d	400	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	300	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics ($T_a = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 10 \mu\text{A}$	40			V
Forward voltage Drop	V_F	$I_F = 20 \text{ mA}$			0.37	
		$I_F = 200 \text{ mA}$			0.6	
Instantaneous Reverse current	I_{RM}	$V_R = 30 \text{ V}$			5	μA
Total capacitance	C_T	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$		50		pF
Reverse recovery time	t_{rr}	$I_F = I_R = 200 \text{ mA}, I_{rr} = 0.1 \times I_R, R_L = 100 \Omega$		10		ns

■ Marking

Marking	S4

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Typical Characteristics

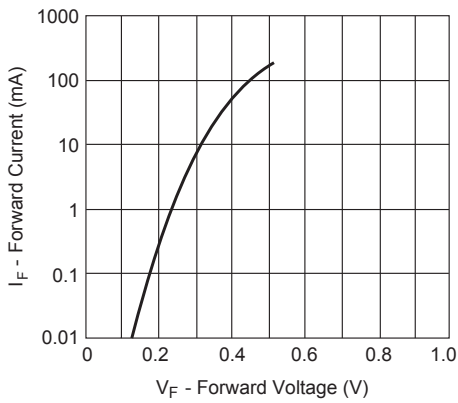


Fig. 1 - Typical Variation of Forward Current vs. Forward Voltage

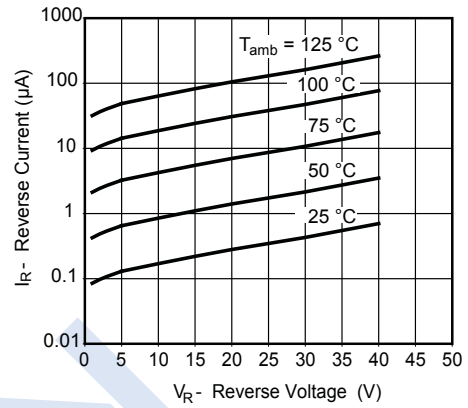


Fig. 3 - Typical Variation of Reverse Current at Various Temperatures

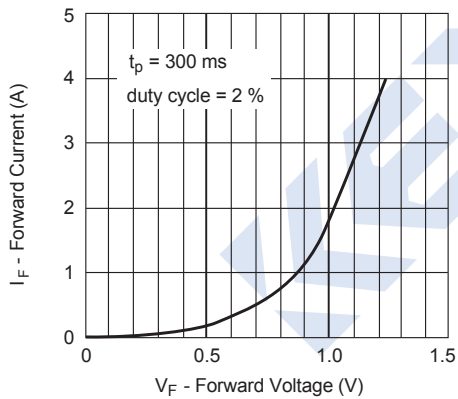


Fig. 2 - Typical High Current Forward Conduction Curve

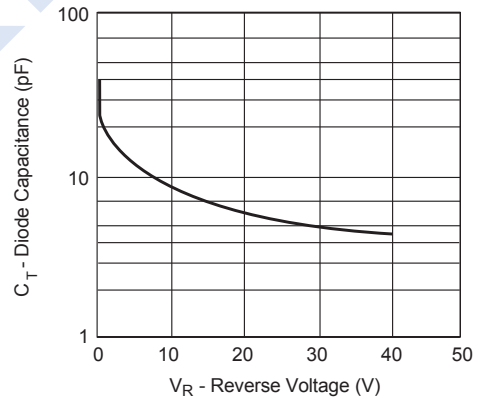


Fig. 4 - Typical Capacitance vs. Reverse Voltage

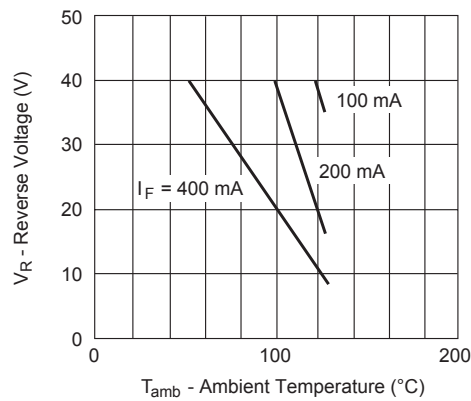


Fig. 5 - Blocking Voltage Deration vs. Temperature at Various Average Forward Currents

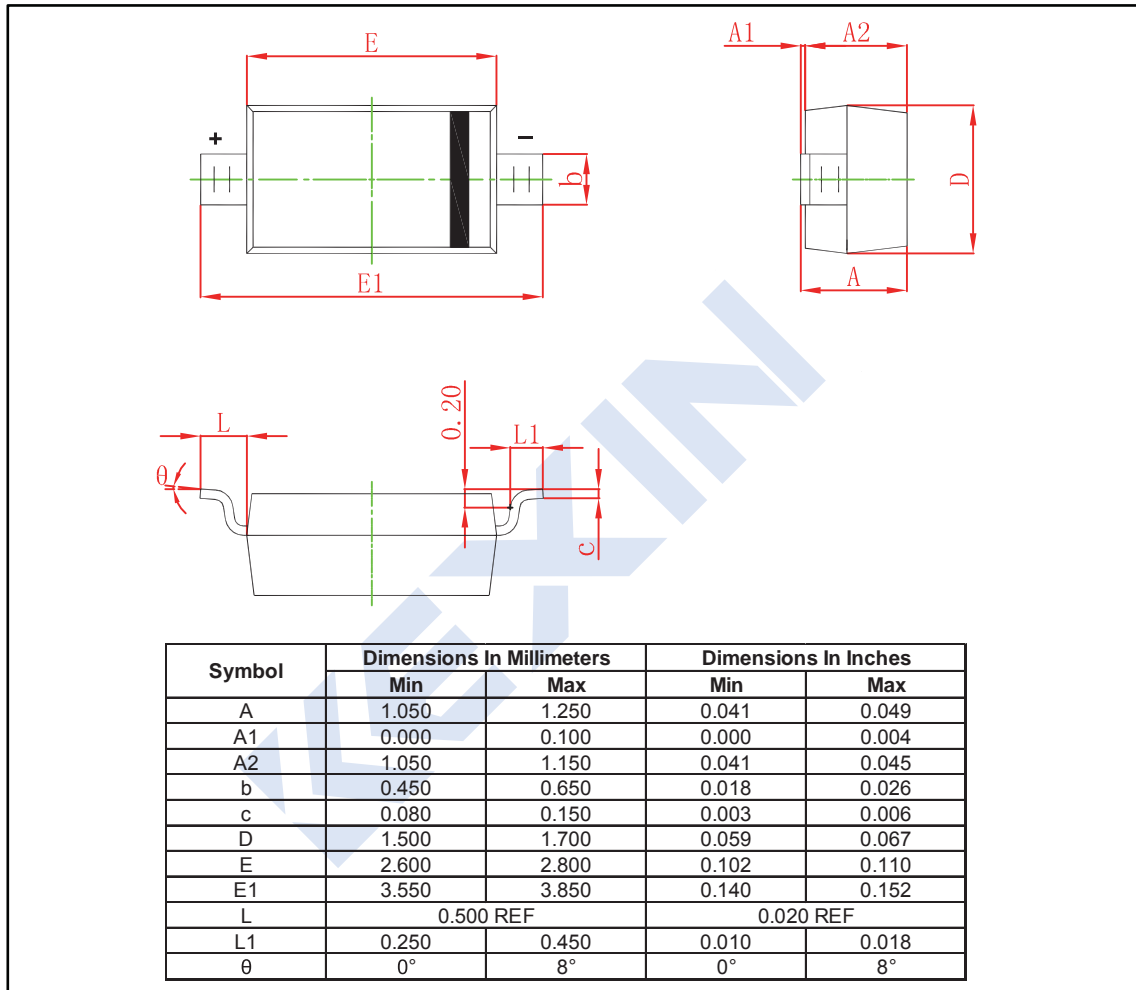
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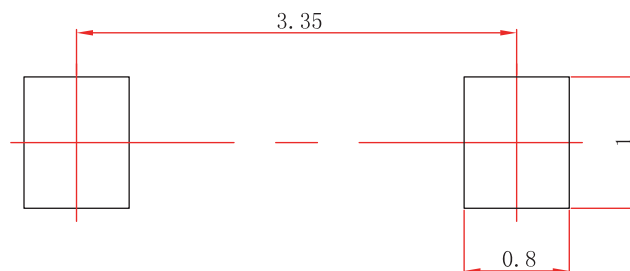
■ Package Outline Dimensions

Plastic surface mounted package; 2 leads

SOD-123



■ The Recommended Mounting Pad Size



Note:

1. Controlling dimension in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.